

# Title AlGaAs, double-heterojunction, visible laser diodes

## RLD-78PP-G1 / RLD-78NP-G1

RLD-78PP-G1 and RLD-78NP-G1 are the semiconductor laser developed for the laser beam printer application.

We have achieved the very small variations of the optical characteristics and low droop by ROHM original Epitaxial growth technology using Molecular Beam Epitaxy.

In addition, they have the appropriate characteristics for sensor application as well.

### ●Applications

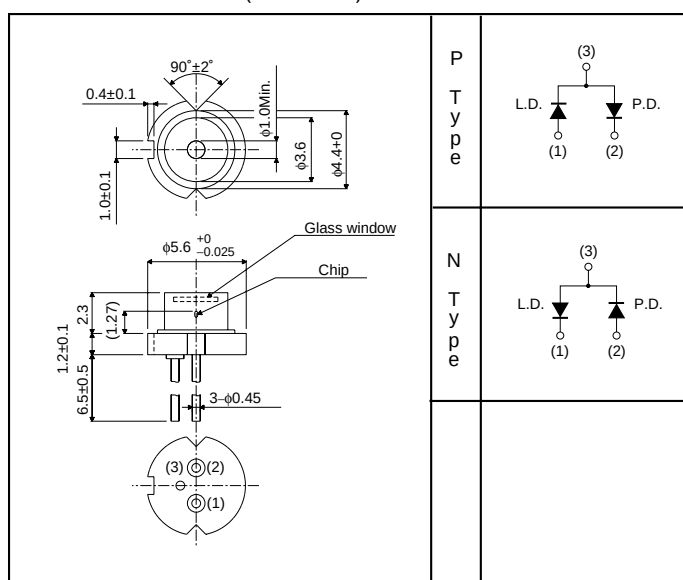
Laser beam printers

Sensors

### ●Features

- 1) Minimum variation of radiation beam angle.
- 2) Low droop.
- 3) High stability wave length.
- 4) Can be driven by single power supply.

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Tc=25°C)

| Parameter             | Symbol         | Limits              | Unit |
|-----------------------|----------------|---------------------|------|
| Output                | Po             | 5                   | mW   |
| Reverse voltage       | Laser          | V <sub>R</sub>      | 2    |
|                       | PIN photodiode | V <sub>R(PIN)</sub> | 30   |
| Operating temperature | Topr           | -10~+60             | °C   |
| Storage temperature   | Tstg           | -40~+85             | °C   |

# Laser Diodes

## ●Electrical and optical characteristics (Ta=25°C)

| Parameter                      | Symbol                                 | Min. | Typ. | Max.     | Unit    | Conditions                  |
|--------------------------------|----------------------------------------|------|------|----------|---------|-----------------------------|
| Threshold current              | $I_{th}$                               | 10   | 25   | 45       | mA      | -                           |
| Operating current              | $I_{op}$                               | 15   | 45   | 65       | mA      | $P_o=3mW$                   |
| Operating voltage              | $V_{op}$                               | -    | 1.9  | 2.3      | V       | $P_o=3mW$                   |
| Differential efficiency        | $\eta$                                 | 0.1  | 0.2  | 0.3      | mW/mA   | $\frac{2mW}{I(3mW)-I(1mW)}$ |
| Monitor current                | $I_m$                                  | 0.3  | 0.55 | 0.9      | mA      | $P_o=3mW$                   |
| Parallel divergence angle      | $\theta_{//}^*$                        | 8    | 11   | 15       | deg     | $P_o=3mW$                   |
| Perpendicular divergence angle | $\theta_{\perp}^*$                     | 25   | 30   | 38       | deg     |                             |
| Parallel deviation angle       | $\Delta\phi_{//}$                      | -    | -    | $\pm 2$  | deg     |                             |
| Perpendicular deviation angle  | $\Delta\phi_{\perp}$                   | -    | -    | $\pm 3$  | deg     |                             |
| Emission point accuracy        | $\Delta X$<br>$\Delta Y$<br>$\Delta Z$ | -    | -    | $\pm 80$ | $\mu m$ | -                           |
| Peak emission wavelength       | $\lambda$                              | 770  | 785  | 795      | nm      | $P_o=3mW$                   |
| Droop                          | $\Delta P$                             | -    | 5    | 10       | %       | $P_o=3mW$                   |

\* $\theta_{//}$  and  $\theta_{\perp}$  are defined as the angle within which the intensity is 50% of the peak value.

## ●Electrical and optical curves

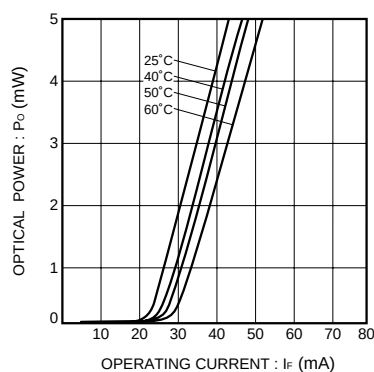


Fig. 1 Optical output vs. operating current

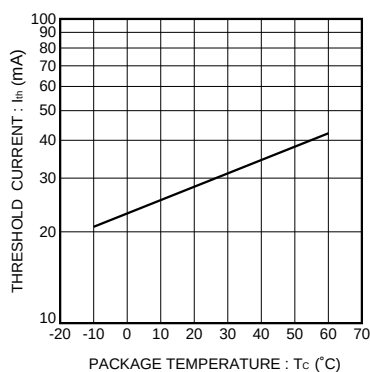


Fig. 2 Dependence of threshold current on temperature

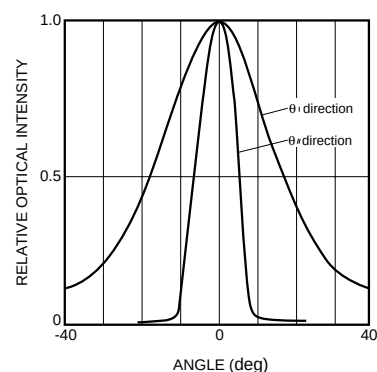


Fig. 3 Far field pattern

Laser Diodes

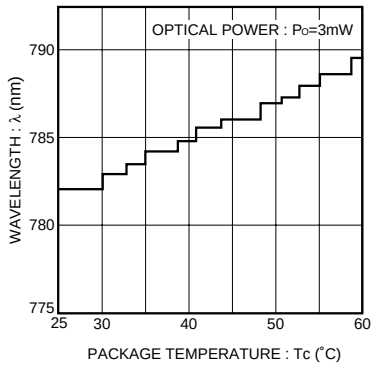


Fig. 4 Dependence of wavelength on temperature

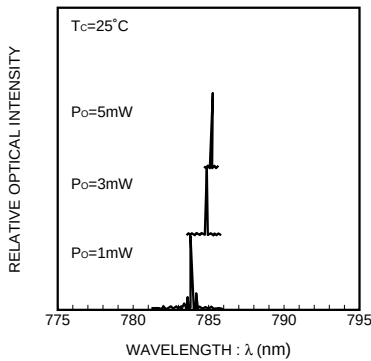


Fig. 5 Dependence of emission spectrum on optical output

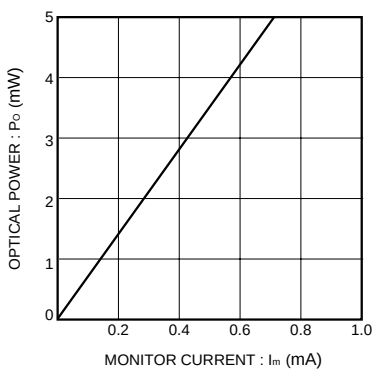


Fig. 6 Monitor current vs. optical output

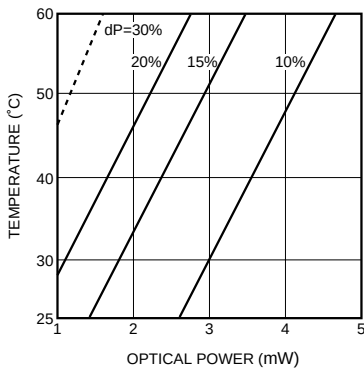


Fig. 7 Temperature vs. output guidelines for various droop percentages

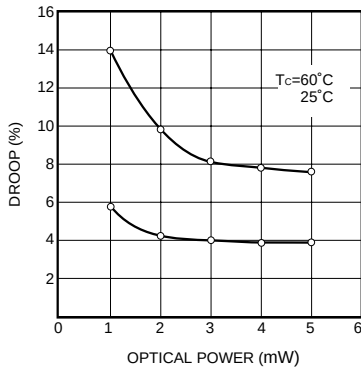


Fig. 8 Dependence of droop on output